

# Substrate Integrated Waveguides for sub-THz Region

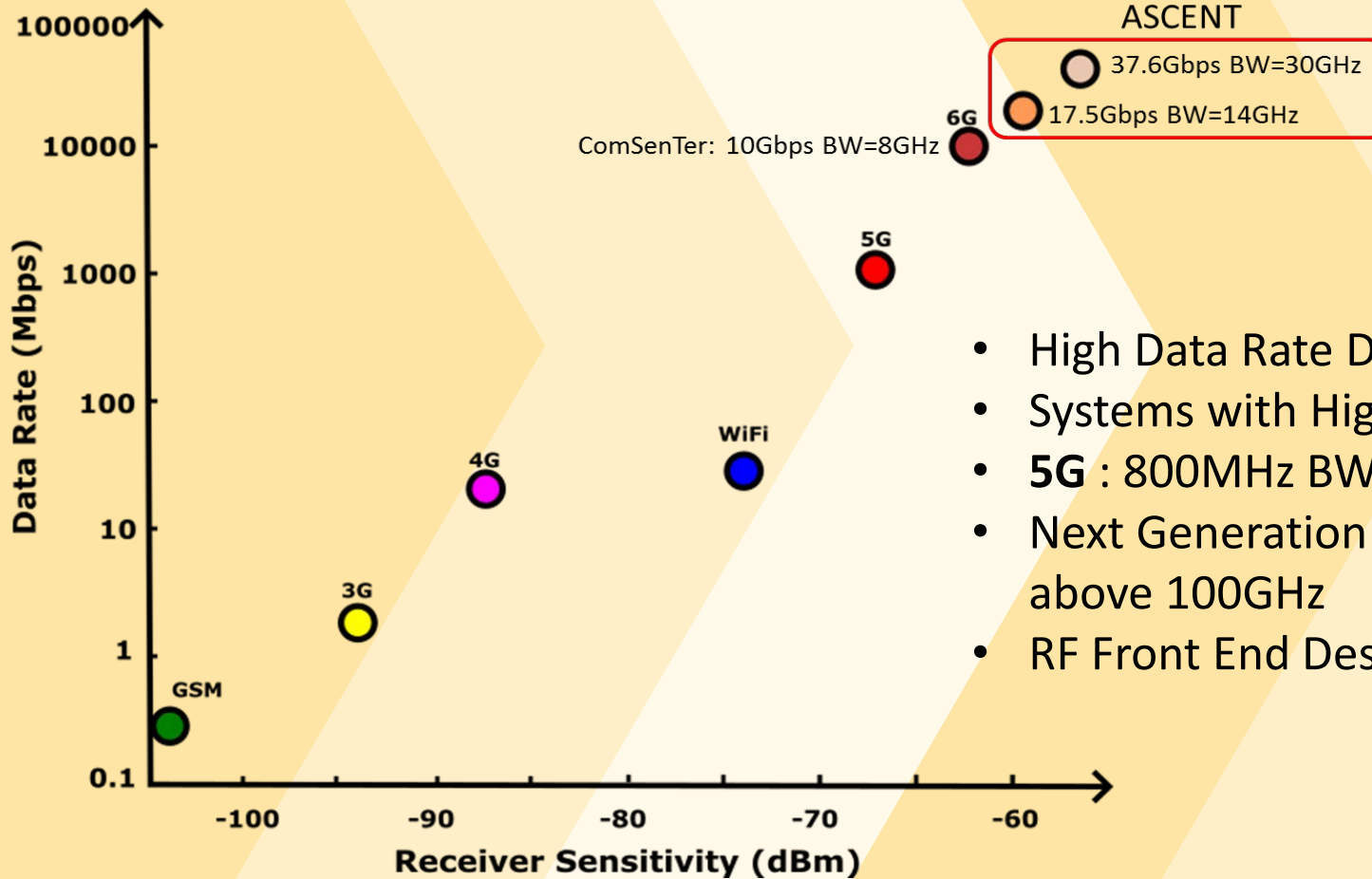
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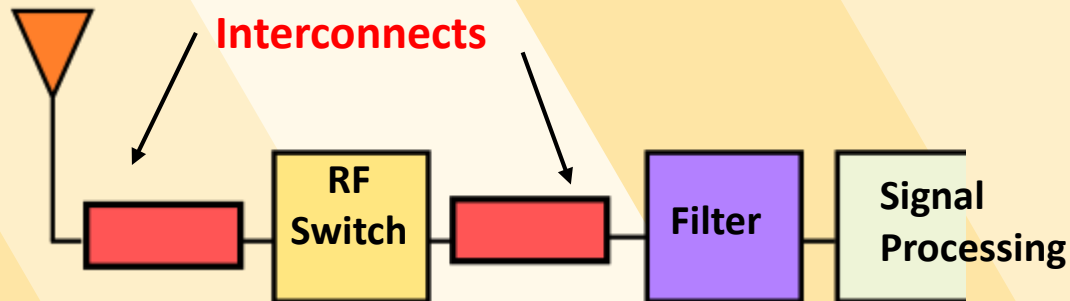


# Next Generation Wireless Systems



- High Data Rate Demands
- Systems with High Bandwidths
- **5G** : 800MHz BW @ 28GHz
- Next Generation Systems → above 100GHz
- RF Front End Design

Antenna

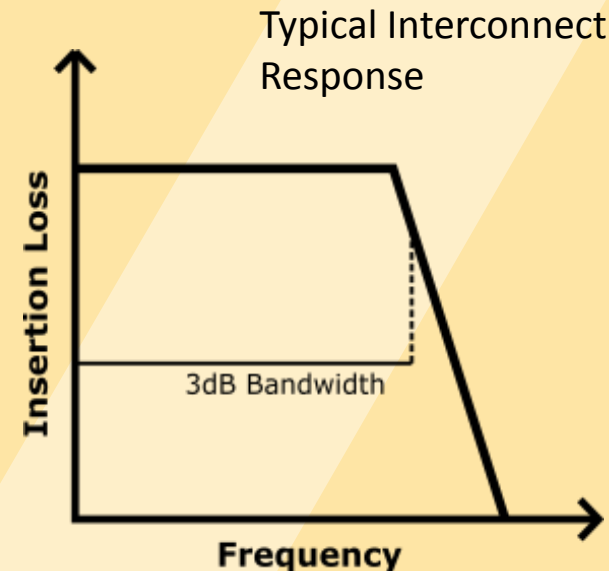


Microstrip Lines (MS) and Coplanar Waveguide (CPW) → traditional interconnects

- Limited bandwidth
- Higher loss based on structure
- Higher Coupling and Crosstalk

**Objective** is to develop new technology for developing high performance passives (interconnects, filters, couplers) in sub-THz region with

- Low Loss
- Zero Cross Talk
- Broadband performance
- High Power Handling capability



# Substrate Integrated Waveguides

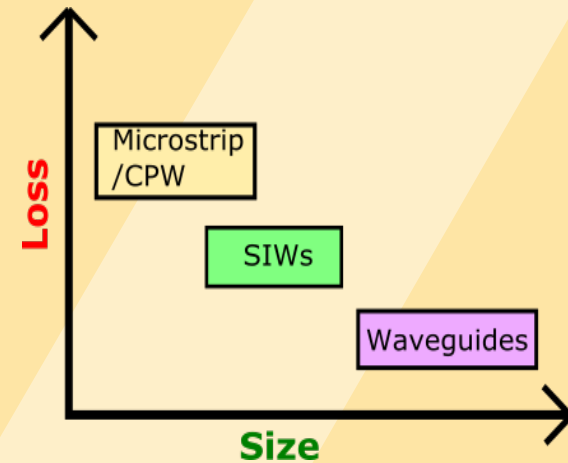
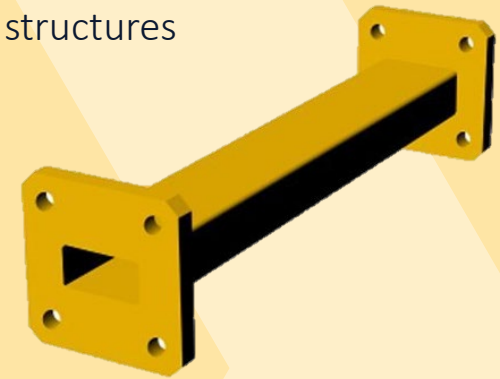
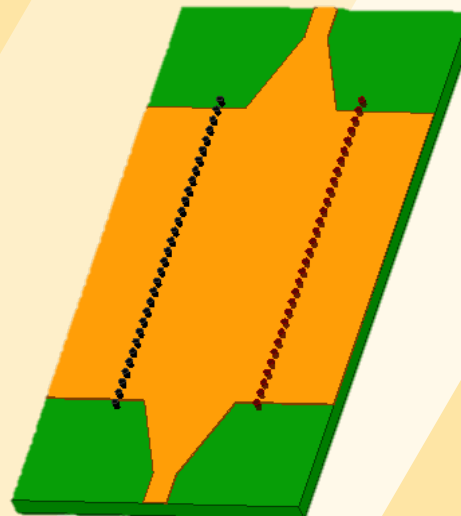
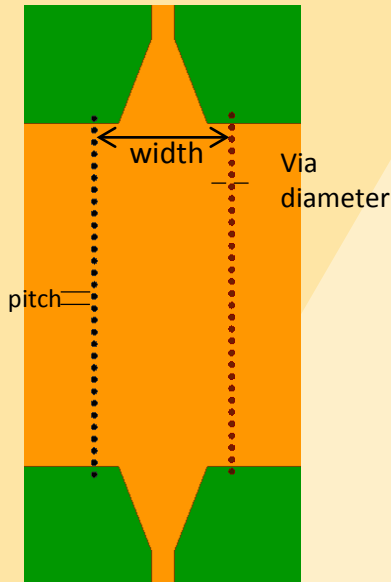
Traditional Waveguides have advantages over Microstrip and CPW lines

## Challenges

High Cost, bulky, Difficult to mass produce, Difficult to integrate with planar structures

SIWs[1] bridge the gap between MS/CPWs and Waveguides

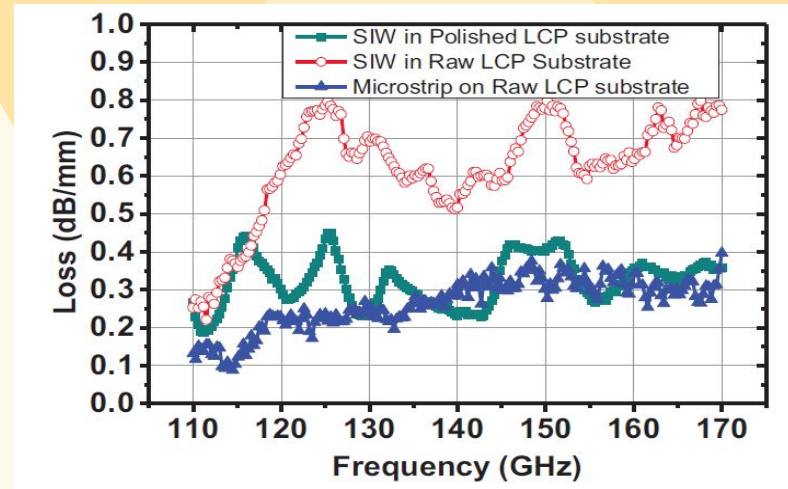
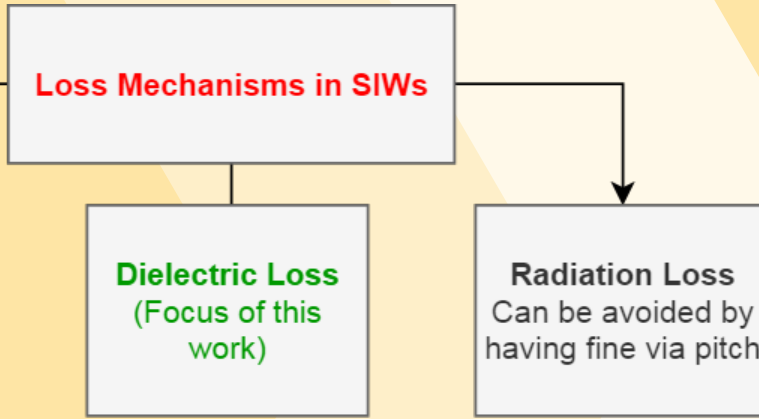
- ❑ Attenuation = 0.3dB/mm (GT work) @ 170GHz
- ❑ 3X-4X higher bandwidth with Zero crosstalk
- ❑ Easier to fabricate and integrate



[1]D Deslandes, K Wu, "Integrated microstrip and rectangular waveguide in planar form"

# SIWs Prior Art

- SIW[2] technology is well known for <40GHz
- Sub-THz region challenges → material losses, surface roughness



## Challenges @ THz

- Use of new low loss materials
- Developing new processes → low cost and easy
- Smooth surface finish
- Looking into ways to reduce dielectric loss

**Material Characterization is important**

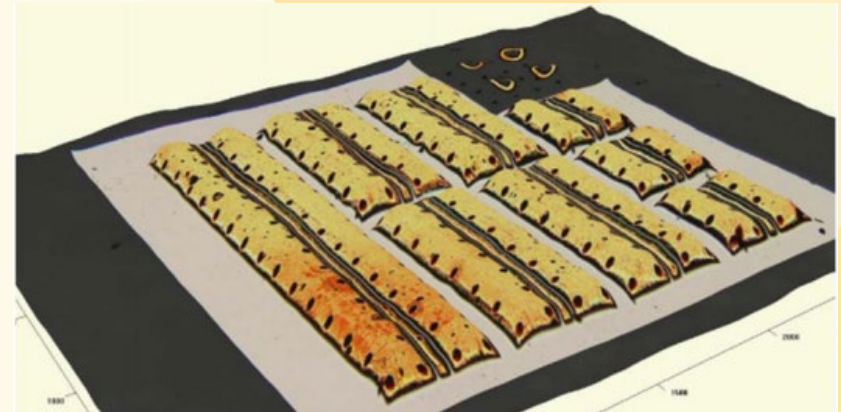
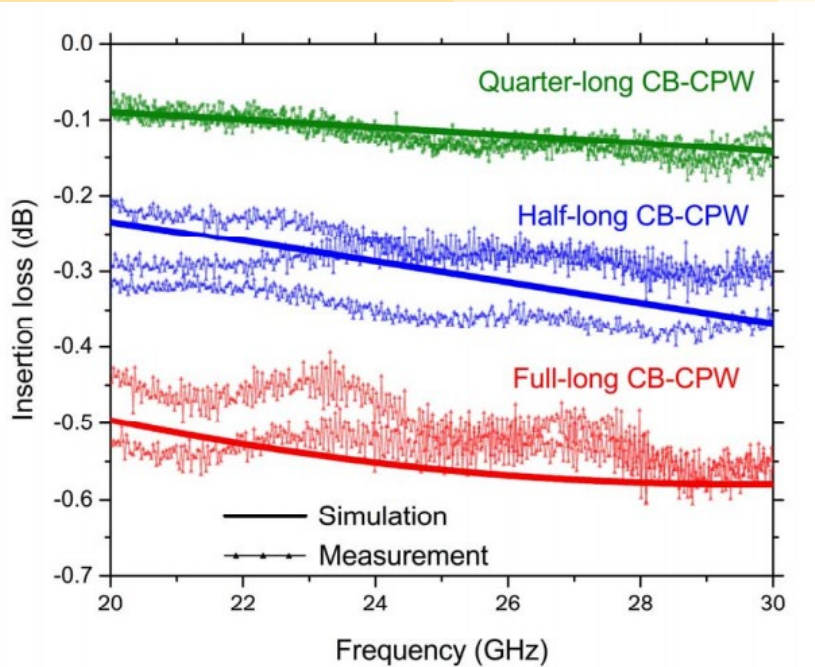
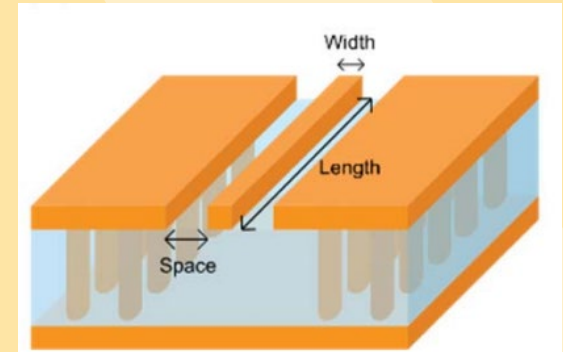
[1] Sensen Li , Ming Yi , Spyridon Pavlidis, Huan Yu, Madhavan Swaminathan, John Papapolymerou et al, RWS, 2017

[2]D Deslandes, K Wu, "Integrated microstrip and rectangular waveguide in planar form"

# Glass Based CPWG Lines 5G-Prior Work

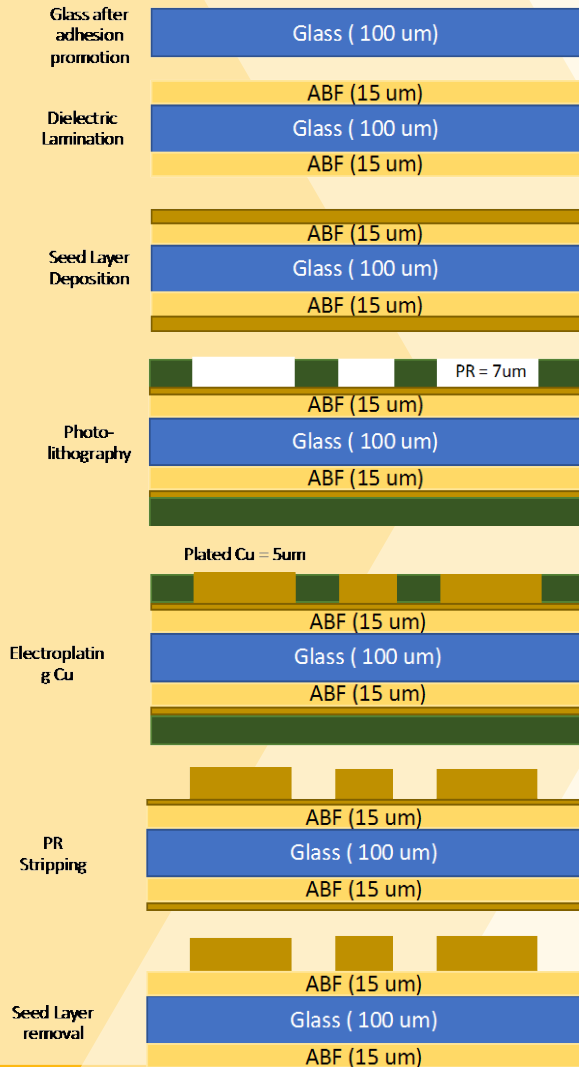
## Characterization of Glass based Transmission Lines for 5G

- CPWG lines
- Measured Insertion loss :0.3dB/mm@ 30GHz

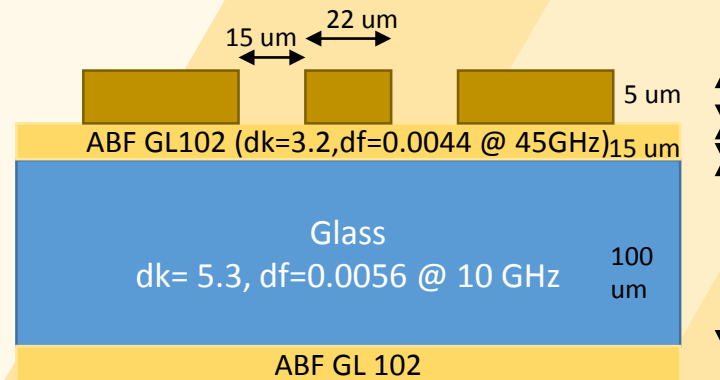


Atom O. Watanabe, Muhammad Ali, Bijan Tehrani, Jimmy Hester, Hiroyuki Matsuura, Tomonori Ogawa, P. Markondeya Raj, Venky Sundaram, Manos M. Tentzeris, Rao R. Tummala "First Demonstration of 28 GHz and 39 GHz Transmission Lines and Antennas on Glass Substrates for 5G Modules," 2017 IEEE 67th Electronic Components and Technology Conference (ECTC), Orlando, FL

## Fabrication Process



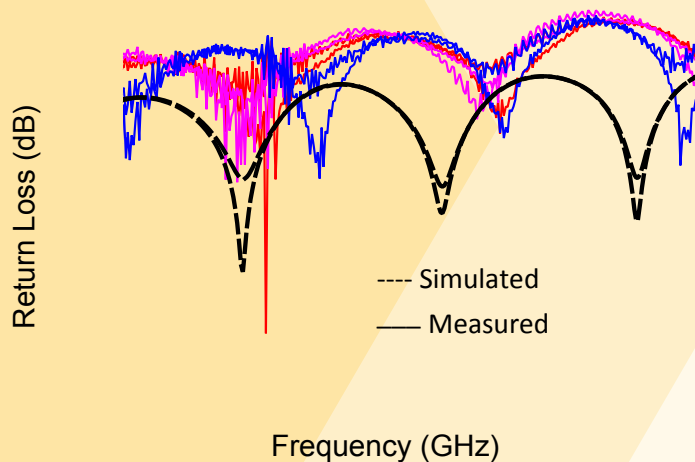
## Fabricated Test Vehicle



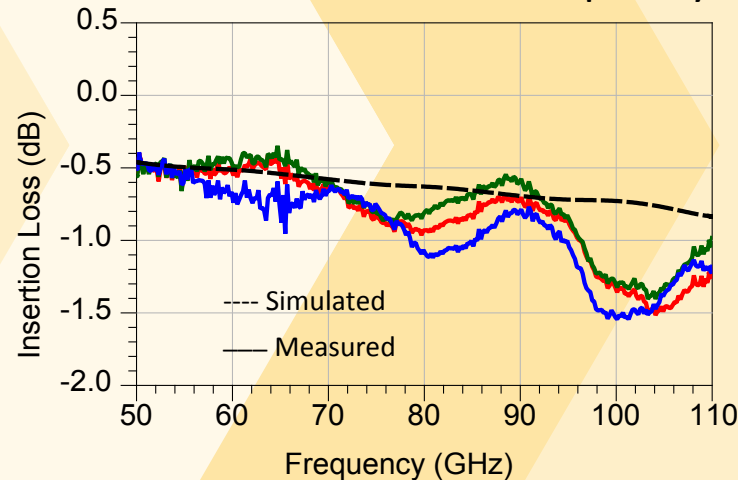
## Preliminary Results

- Scattering Parameters of 5mm long designed CPW Lines were measured from 50GHz to 110GHz

Return Loss vs Frequency



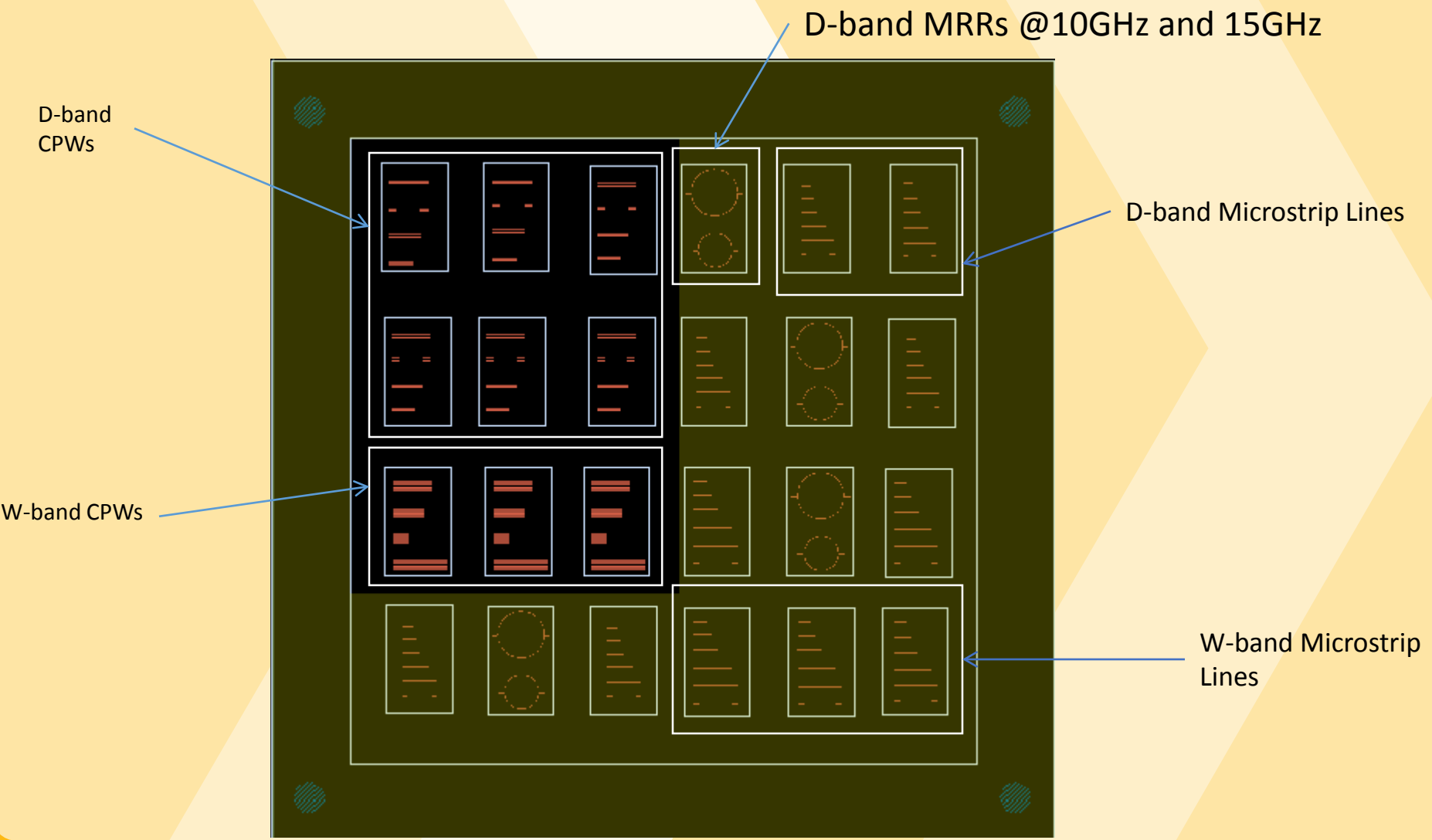
Insertion Loss vs Frequency



- The measured results show insertion loss of 0.2dB/mm at 110GHz
- Good electrical performance
- Merits further investigation and characterization



## Glass and Astra Characterization Test Vehicle

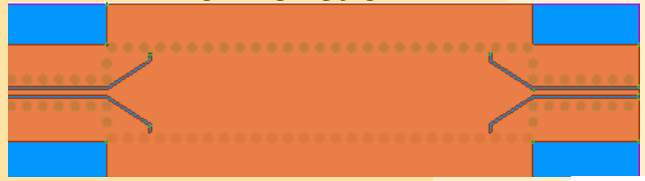


- Characterization of Glass Based SIWs
- Glass Based SIW Resonators

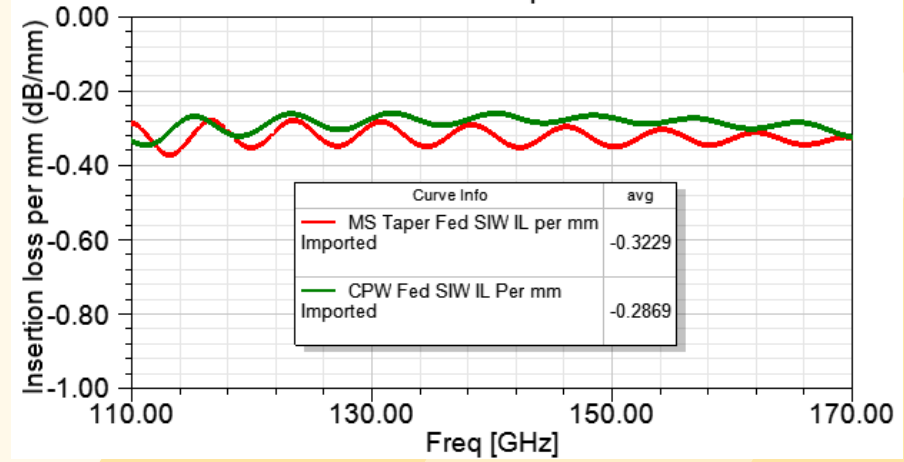
Microstrip Fed SIW



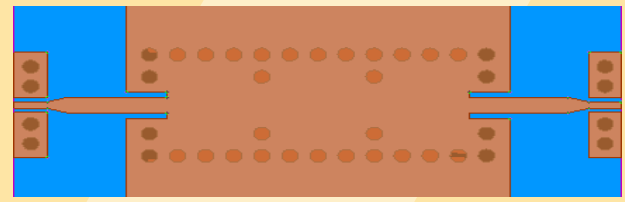
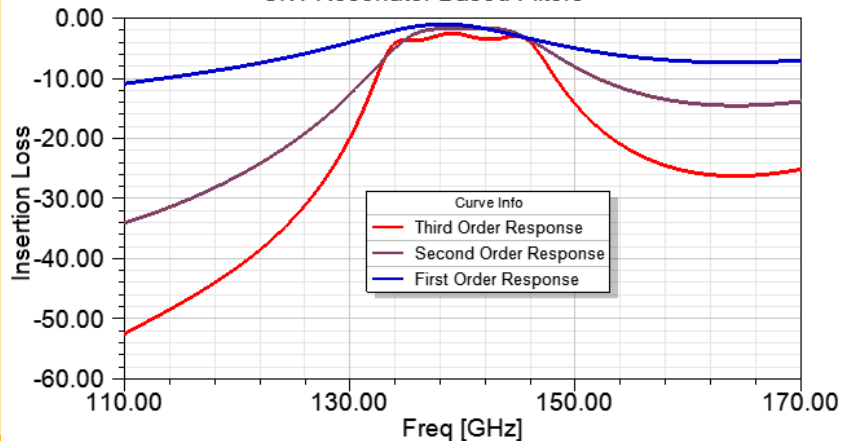
CPWG Fed SIW



Insertion Loss Comparison



SIW Resonator Based Filters



3<sup>rd</sup> Order SIW Resonator

- ❑ Fabrication of Test Vehicles for characterization of Glass and Astra
- ❑ Measurements for characterization
- ❑ Process planning for development of Sub-THz SIW Technology
- ❑ Characterization of solid SIWs on Astra and Glass
- ❑ Working towards making other passive microwave components like filters, couplers, phase shifters and power dividers using SIW as a building block

# Timeline

	2019	2020				2021		
	Q4	Q1	Q2	Q3	Q4	Q1	Q2	Q3
done	Glass CPWs in W-band	[Green bar]						
progress	Glass Characterization	[Yellow bar with red star]						
Plan	Solid SIWs Characterization	[Blue bar]						
	SIW based Passives TV	[Blue bar]						
	Sub-THz SIWs Characterization	[Blue bar]						
	Sub-THz SIWs Based Passives	[Blue bar]						

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